

Low-Voltage CMOS 16-Bit Transparent Latch

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

MC74LCX16373

The MC74LCX16373 is a high performance, non–inverting 16–bit transparent latch operating from a 2.3 V to 3.6 V supply. The device is byte controlled. Each byte has separate Output Enable and Latch Enable inputs. These control pins can be tied together for full 16–bit operation. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX16373 inputs to be safely driven from 5.0 V devices.

The MC74LCX16373 contains 16 D-type latches with 3-state 5.0 V-tolerant outputs. When the Latch Enable (LEn) inputs are HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The 3-state outputs are controlled by the Output Enable (\overline{OEn}) inputs. When \overline{OE} is LOW, the outputs are enabled. When \overline{OE} is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches.

Features

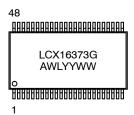
- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.4 ns Maximum t_{pd}
- 5.0 V Tolerant Interface Capability With 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (20 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - ♦ Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

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MARKING DIAGRAM

CASE 1201



A = Assembly Location

WL = Wafer Lot
 YY = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX16373DTG	TSSOP-48 (Pb-Free)	39 Units / Rail
M74LCX16373DTR2G	TSSOP-48 (Pb-Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

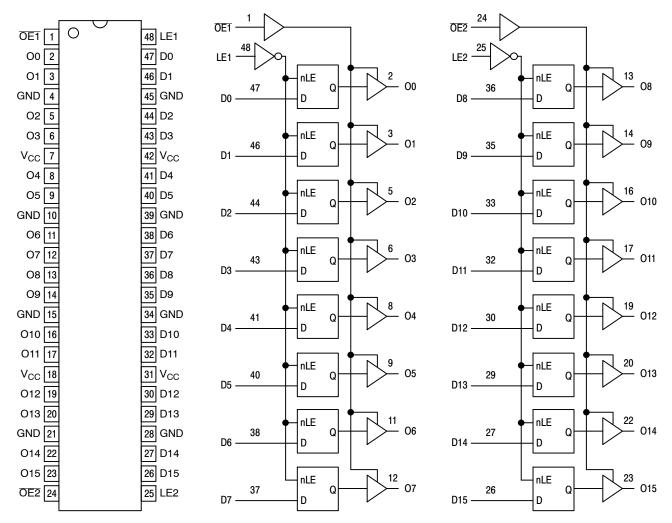


Figure 1. Pinout: 48-Lead (Top View)

Figure 2. Logic Diagram

Table 1. PIN NAMES

Pins	Function	
OEn	Output Enable Inputs	
LEn	Latch Enable Inputs	
D0-D15	Inputs	
O0-O15	Outputs	

TRUTH TABLE

	Inputs		Outputs	Inputs			Outputs
LE1	OE1	D0:7	O0:7	LE2	OE2	D8:15	O8:15
Х	Н	Х	Z	Х	Н	Х	Z
Н	L	L	L	Н	L	L	L
Н	L	Н	Н	Н	L	Н	Н
L	L	Х	00	L	L	Х	00

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

 $X = High or Low Voltage Level and Transitions Are Acceptable; for <math>I_{CC}$ reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{\parallel} \le +7.0$		V
V _O	DC Output Voltage	$-0.5 \le V_{O} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State. (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	−65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State) (3-State)	0 0		V _{CC} 5.5	V
Іон	$\begin{array}{l} \text{HIGH Level Output Current} \\ \text{$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$} \\ \text{$V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$} \\ \text{$V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$} \end{array}$			-24 -12 -8	mA
I _{OL}	LOW Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T _A	Operating Free-Air Temperature	-55		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Units
V _{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		1
V _{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	1
l _{OZ}	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5	μΑ
I _{OFF}	Power Off Leakage Current	V _{CC} = 0, V _{IN} = 5.5 V or V _{OUT} = 5.5 V		10	μΑ
I _{IN}	Input Leakage Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		±5	μΑ
I _{CC}	Quiescent Supply Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		20	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μА

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 $\Omega)$

			$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$						
			V _{CC} = 3.3 C _L = 9	V ± 0.3 V 50 pF	V _{CC} =		V _{CC} = 2.5 C _L = 3	V ± 0.2 V 30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t _{PLH} t _{PHL}	Propagation Delay D _n to O _n	1	1.5 1.5	5.4 5.4	1.5 1.5	5.9 5.9	1.5 1.5	6.5 6.5	ns
t _{PLH} t _{PHL}	Propagation Delay LE to O _n	3	1.5 1.5	5.5 5.5	1.5 1.5	6.4 6.4	1.5 1.5	6.6 6.6	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	6.1 6.1	1.5 1.5	6.5 6.5	1.5 1.5	7.9 7.9	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	6.0 6.0	1.5 1.5	6.3 6.3	1.5 1.5	7.2 7.2	ns
t _s	Setup Time, HIGH or LOW D ⁿ to LE	3	2.5		2.5		3.0		ns
t _h	Hold Time, HIGH or LOW Dn to LE	3	1.5		1.5		2.0		ns
t _w	LE Pulse Width, HIGH	3	3.0		3.0		3.5		ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

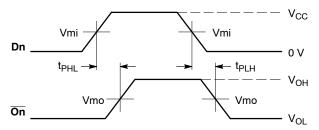
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$\begin{array}{c} V_{CC} = 3.3 \text{ V}, \text{ C}_{L} = 50 \text{ pF}, \text{ V}_{IH} = 3.3 \text{ V}, \text{ V}_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V}, \text{ C}_{L} = 30 \text{ pF}, \text{ V}_{IH} = 2.5 \text{ V}, \text{ V}_{IL} = 0 \text{ V} \end{array}$		-0.8 -0.6		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

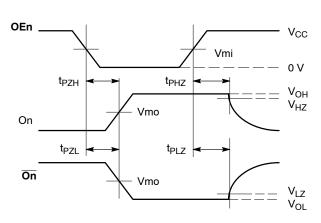
CAPACITIVE CHARACTERISTICS

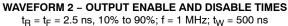
Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	20	pF

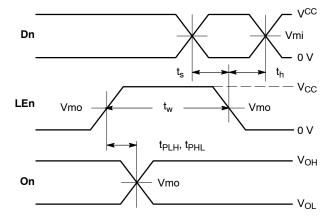


WAVEFORM 1 - PROPAGATION DELAYS

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$







WAVEFORM 3 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns except when noted

Figure 3. AC Waveforms

Table 2. AC WAVEFORMS

		V _{CC}					
Symbol	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V				
Vmi	1.5 V	1.5 V	V _{CC} / 2				
Vmo	1.5 V	1.5 V	V _{CC} / 2				
V_{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V				
V_{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V				

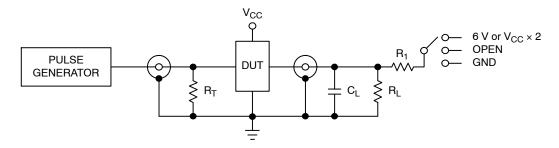


Figure 4. Test Circuit

Table 3. TEST CIRCUIT

Test	Switch
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at $V_{CC} = 3.3 \pm 0.3 \text{ V}$ 6 V at $V_{CC} = 2.5 \pm 0.2 \text{ V}$
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

C_L = 5 capacitance) = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe

 C_L = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω) = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent (includes jig and probe

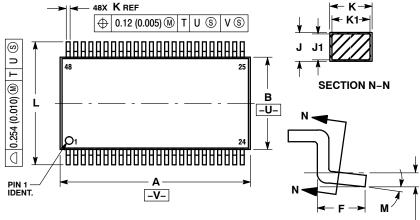




TSSOP-48 **CASE 1201 ISSUE B**

DETAIL E 0.25 (0.010)

DATE 06 JUL 2010

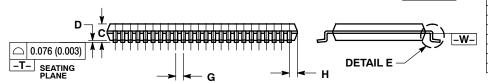




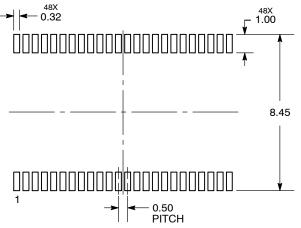
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS
- SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	12.40	12.60	0.488	0.496	
В	6.00	6.20	0.236	0.244	
С		1.10		0.043	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.50	BSC	0.0197 BSC		
Н	0.37		0.015		
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.17	0.27	0.007	0.011	
K1	0.17	0.23	0.007	0.009	
L	7.95	8.25	0.313	0.325	
M	0 0	00	0 0	00	



RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot

YY = Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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